

Data Sheet July 1999 File Number 4762

Radiation Hardened Hex D-Type Flip-Flop with Reset

The Radiation Hardened ACS174MS is a Hex D-Type Flip-Flop with Reset. Information at the D input is transferred to the Q output on the positive-going transition of the clock. All six flip-flops are controlled by a common clock (CP) and a common reset ($\overline{\text{MR}}$). Resetting is accomplished by a LOW level independent of the clock. All inputs are buffered and the outputs are designed for balanced propagation delay and transition times.

The ACS174MS is fabricated on a CMOS Silicon on Sapphire (SOS) process, which provides an immunity to Single Event Latch-up and the capability of highly reliable performance in any radiation environment. These devices offer significant power reduction and faster performance when compared to ALSTTL types.

Specifications for Rad Hard QML devices are controlled by the Defense Supply Center in Columbus (DSCC). The SMD numbers listed below must be used when ordering.

Detailed Electrical Specifications for the ACS174MS are contained in SMD 5962-98634. A "hot-link" is provided on our homepage for downloading. http://www.intersil.com/spacedefense/spaceselect.htm

Features

- QML Qualified Per MIL-PRF-38535 Requirements
- 1.25 Micron Radiation Hardened SOS CMOS
- Radiation Environment
 - Latch-Up Free Under Any Conditions

 - SEU LET Threshold>100MeV/(mg/cm²)
- Input Logic Levels. . . . $V_{IL} = (0.3)(V_{CC}), V_{IH} = (0.7)(V_{CC})$
- Quiescent Supply Current 10μA (Max)

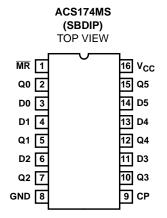
Applications

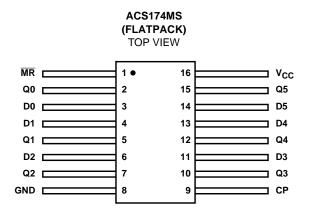
- · High Speed Control Circuits
- Sensor Monitoring
- · Low Power Designs

Ordering Information

ORDERING NUMBER	INTERNAL MARKETING NUMBER	TEMP. RANGE (°C)	PACKAGE	DESIGNATOR
5962F9863401VCC	ACS174DMSR-03	-55 to 125	16 Ld SBDIP	CDIP2-T16
ACS174D/SAMPLE-03	ACS174D/SAMPLE-03	25	16 Ld SBDIP	CDIP2-T16
5962F9863401VXC	ACS174KMSR-03	-55 to 125	16 Ld Flatpack	CDFP4-F16
ACS174K/SAMPLE-03	ACS174K/SAMPLE-03	25	16 Ld Flatpack	CDFP4-F16
5962F9863401V9A	ACS174HMSR-03	25	Die	NA

Pinouts





Die Characteristics

DIE DIMENSIONS:

Size: 2390µm x 2390µm (94 mils x 94 mils) Thickness: $525\mu m \pm 25\mu m$ (20.6 mils ± 1 mil) Bond Pad: 110μm x 110μm (4.3 x 4.3 mils)

METALLIZATION: AI

Metal 1 Thickness: 0.7μm ±0.1μm Metal 2 Thickness: 1.0μm ±0.1μm

SUBSTRATE POTENTIAL

Unbiased Insulator

PASSIVATION:

Type: Phosphorous Silicon Glass (PSG)

Thickness: 1.30μm ±0.15μm

SPECIAL INSTRUCTIONS

Bond V_{CC} First

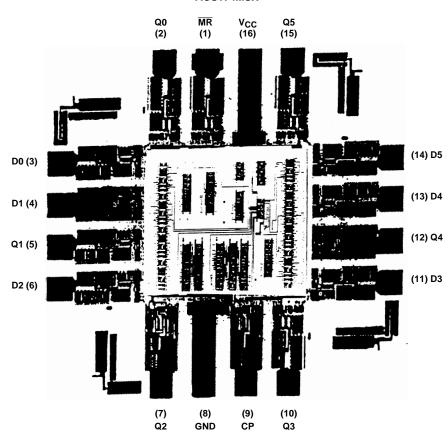
ADDITIONAL INFORMATION:

Worst Case Current Density: <2.0 x 10⁵ A/cm²

Transistor Count: 358

Metallization Mask Layout

ACS174MSX



All Intersil semiconductor products are manufactured, assembled and tested under ISO9000 quality systems certification.

Intersil semiconductor products are sold by description only. Intersil Corporation reserves the right to make changes in circuit design and/or specifications at any time without notice. Accordingly, the reader is cautioned to verify that data sheets are current before placing orders. Information furnished by Intersil is believed to be accurate and reliable. However, no responsibility is assumed by Intersil or its subsidiaries for its use; nor for any infringements of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Intersil or its subsidiaries.

For information regarding Intersil Corporation and its products, see web site www.intersil.com

Sales Office Headquarters

NORTH AMERICA

Intersil Corporation P. O. Box 883, Mail Stop 53-204 Melbourne, FL 32902

TEL: (321) 724-7000 FAX: (321) 724-7240

EUROPE

Intersil SA Mercure Center 100. Rue de la Fusee 1130 Brussels, Belgium TEL: (32) 2.724.2111 FAX: (32) 2.724.22.05

ASIA

Intersil (Taiwan) Ltd. 7F-6, No. 101 Fu Hsing North Road Taipei, Taiwan Republic of China TEL: (886) 2 2716 9310 FAX: (886) 2 2715 3029